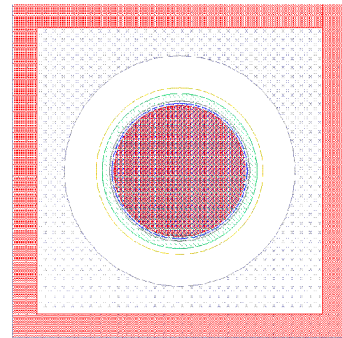


**2KG028075YQ SWITCHING DIODE CHIPS**
**DESCRIPTION**

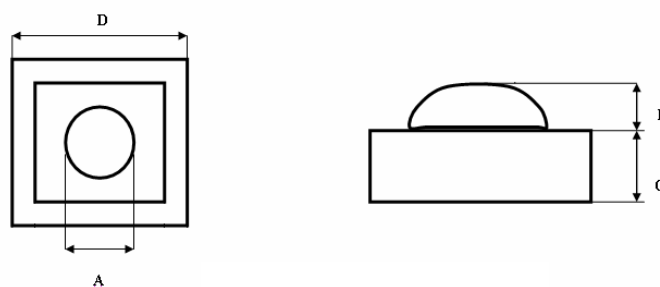
- 2KG028075YQ is a high speed switching diode chip fabricated in planar technology.
- This chip can be encapsulated as 1N4148 switching diode.
- When the chip is selected glass package, the chip thickness is 120 $\mu$ m, and the top electrodes material is Ag bump, the back-side electrodes material is Ag.
- Chip size: 0.28 X 0.28 (mm<sup>2</sup>).



2KG028XXX CHIP TOPOGRAPHY

**2KG028075YQ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C)**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA.	--	--	1.0	V
		I <sub>F</sub> =100mA.	0.62	0.9	1.2	V
Reverse voltage	V <sub>BR</sub>	I <sub>B</sub> =100 $\mu$ A.	100	120	--	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =20V.	--	--	25	nA
		V <sub>R</sub> =75V.	--	--	5	$\mu$ A
Diode Capacitance	C <sub>d</sub>	f=1MHz; V <sub>R</sub> =0.	--	1.9	4	pF
Reverse Recovery Time	t <sub>rr</sub>	When switched from I <sub>F</sub> =10mA to V <sub>R</sub> =6V; R <sub>L</sub> =100 $\Omega$ ; measured at I <sub>R</sub> =1mA.	--	--	4	ns

**2KG028075YQ APPEARANCE (Top side material is Ag ball)**


Chip Appearance Diagram

Parameter	Symbol	Min.	Type	Max.	Unit
Chip Size	D	240	--	260	$\mu$ m
Chip Thickness	C	100	--	140	$\mu$ m
Bump Diameter	A	190	--	225	$\mu$ m
Bump Height	B	60	80	90	$\mu$ m
Scribe Line Width	/	--	40	--	$\mu$ m